Module 1: Packaging Evolution: From Basics to 3D Integration

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L1: Introduction To Semiconductor Packaging

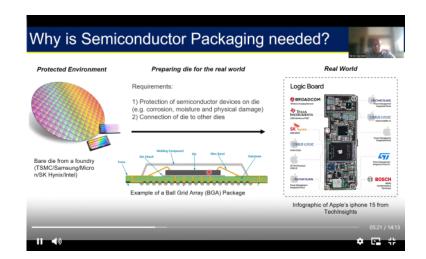
By Tarun Agrawal
IIT Gandhinagar

Why Packaging Is Needed?

So, individual chips are cut out from wafers. They are built in a protected environments.

But when used, these ICs are exposed to the real world.

- 1. Packaging enables the die to work in the real world (Corrosion, Physical damage, moisture etc.)
- 2. Allow connection to other dies



So here, the black outer casing is not the package, but the moulding compound. The IC is placed within the moulding compound & we use wire bonds to connect it to the substrate. Wire bond allows us to connect to BGA, which can be used to connect to a system.

So, packaging brings personality to an intelligent chip

Design is the first step in this process, we give designs to a foundry, who manufacture it. Post manufacturing, we test the wafer, package it & test it in packages & test. Tested ICs are sent for assembly.

IDMs: Design, Foundry & Packaging: End to End (Intel, Samsung, Micron, SKHynix, TI, ST) But for fabless companies:

- 1. Fabless Design Centric Orgs (Qualcomm, nVidia, AMD, Apple)
- 2. Foundry: Wafer Mfg (TSMC, Global Foundries)
- OSAT (Outsourced Semiconductor Assembly & Test): Packaging & Testing of all wafers they
 receive (ASE, Amkor, JCET, PTI, UTAC, TSMC etc.)

Packaging and Testing industry IDM (Integrated Device Manufacturer) (Intel, Samsung, Micron, Renesas, SKHynix, TI, ST Micro etc.) (Qualcomm, Nvidia, AMD, Apple, (ASE, Amkor, JCET, PTI, UTAC, TSMC etc.) (TSMC, Global Foundries etc.) MediaTek and many others..) **Fabless** OSAT (Outsourced Semiconductor Assembly and Test) Foundry Upcoming in India: Micron, CG Semiconductor Packaging and testing Power+Renesas, TATA Electronics, and design-centric manufacturing semiconductors and wafers Kaynes Semiconductor -centric Source: SK Hynix NEWSROOM, Semiconductor Back-end process, Episode 1

Upcoming Units in India: Micron, CG Powers + Renesas, Tata Electronics, Kaynes Semiconductor

L2: Understanding Package Requirements & Foundational Package Types

Silicon Development Lifecycle:

- 1. Product Requirements
- Design
- 3. Manufacturing
- Testing
- 5. Debugging
- 6. In-field operation

Course Structure:

- 1. Intro
- 2. Package Manufacturing
- 3. Testing: Reliability & QA
- Design w.r.t Electrical, Thermal & Mechanical Constraints
- 5. Future Trends

How do we choose the right package: It primarily depends on the application Other important factors:

- Bandwidth: Should be able to support required connections / IO.
 Thermal Dissipation: Heat must be dissipated away from IC, in addition to operating temps.
- Form Factors: How large can the package be
- Reliability & Durability: Based on operating environments
 Cost: Most important factor: Must optimize

Typical Package Structure:

So, 4 basic components:

- 1. Die: The actual silicon chip
- Carrier: The layer over which the die is placed. Can be substrate or other materials
 System Boards: The PCB over which the carrier is placed.
- Moulding: External layer which protects the die from environmental factors.

Need to establish connections from die to carrier & carrier to system board.

Two Families of Packages:

- 1. Through Hole Packages: DIP, SIP, PGA, Since have pins: Have larger size
- 2. Surface Mount Technology: Allows us to optimally use the available area of the package Use pads below or around the IC.

QFP & QFN: Quad flat packages. N - No lead, P - Pins

BGA Class: Ball grid Array. P - Plastic. Use solder balls

LGA: Land Grid Array

CSP: Chip Scale Package: Similar to BGA, but package size is close to die size.

L3: Evolving Package Architecture - Single Chip to Multi-Chip Modules

So most packages covered till now only have a single die on package.

This changed with the introduction of multi-die packages

They are called: MCM : Multichip Packages. E.g.: Intel Broadwell

PoP: Package-On-Package: Tack & pass interconnect through the lower package.

CoWoS: Advanced packaging seen in Nvidia H100

Options for Carriers:

Started with lead frames : Metallic package backframes with epoxy shells.

Laminates: Stacked layers of material glued together

Modern Materials: Plastic, Ceramics, Organic RDL, Silicon & Glass Ideally, choice of carrier is dictated by operating environment

2 Modes of interconnects:

- 1. Wire Bonding: Use wires to connect die points to package
- 2. Bumps: Use Solder balls

Anatomy of Packages:

A. Leadframe

1. Lead frame:

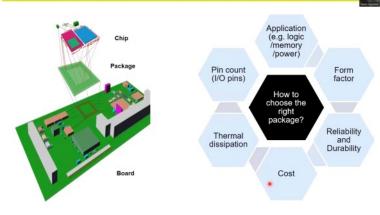
Here, we have a metal support frame on which the die is glued to. We use wire bonds to connect die to pins, which may be stamped from the same sheet. We apply moulding compound on either sides & bend the leads

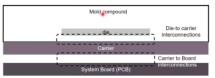
2. QFN: Quad Flat No Lead

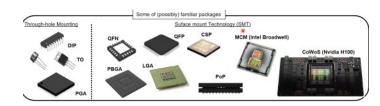
Bigger package with connections on all four sides. Similar to lead frame, we have a metallic frame & we use a die-attach to hold the die. We connect the wires to pads & encase the moulding May add thermal pads too.

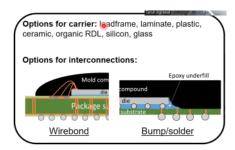
3. Leadframe CSP: Small die size packages

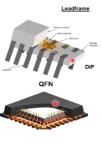
Product requirements













3. Leadframe CSP: Small die size packages

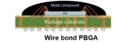
4. Leadframe-QFP: Quad Flat Package with Pins Die is placed on a lead frame, but we have physical pins





B. Laminate:

1. Wire Bond PBGA (Plastic Ball Grid Array) Die is placed on a laminate, we wire bond connections to the ball grid array & add mould

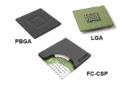


2. Flip Chip PBGA:

Here, we flipped the die, now bumps will connect to solder balls of the substrate. We also have an epoxy underfill



- 3. Flip Chip CSP: Same as flip chip, but smaller footprint
- 4. LGA: Land grid Array: Instead of bumps, we use pins & an array of contacts



C. Advanced Package Substrates

2D Integration:

On the same substrate (Maybe FCBGA), we connect two dies. Better than having two substrates, but for communication between the dies, need to pass signal from die to BGA & then to the other die



2. 2.1D Integration:

Eliminates the longer connections by adding a redistribution layer between die & substrate. The RDL has internal connections which offer a shorter pathway.

Intermediate layers allow us to fan out connections when connection density increases.



2.1D





2.3D

Why not called 3D?: As dies are still not stacked

Note:

4. 2.5D Integration:

3. 2.3D Integration:

Here, we need to fan out high density connections & offer minimal latency. To achieve this, we add a layer of active silicon as the interposer.

L4: Interposer Redistribution Layer & 2.5D/3D Packaging Approaches

Here, we place an organic interposer between the FC & FCBGA substrate.







SoC: System on Chip HBM: High Bandwidth Memory

Pitch Bump: The spacing between adjacent bumps in BGA.

Source: Semiconductor Advanced Packaging, John H. Lau Semiconductors (Regular, SoC, Chiplets etc.) COB 2.5D 2.1D 2.3D

When integrating a die into a design, we deal with 3 levels:

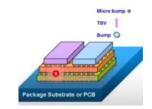
- Die Level
- 2. Substrate Level
- System PCB Level

Why not place a chip directly on PCB: Can be done: Called CoB: Chip On Board

L-5: Comparative Analysis & Selecting The Right Package Solution

3D Integration:

Dies stacked on dies with connections going across them



Comparison								
IC package Type	MMM.	E TOTAL STATE				Die 1 Die 2 FCBGA Substrate	Die 1 Tarun Agraw RDL Layer FCBGA Substrate	Si Interposer FCBGA Substrate
Pros	Low cost, easy to manually assemble, durable	Compact, good thermal performance, lightweight	Higher pin density, ease of inspection, ease of solderability	Higher pin count, good electrical and thermal performance	Reduced package size, higher electrical performance at lower cost	Higher level of integration, better performance, and power efficiency	Higher density I/O and routing at lower cost	high I/O throughput, hetero- geneous integration, lower latency
Cons	Bigger size, low pin count, incompatible with automated assembly	Testing accessibility, Reparability, smaller I/O pins than QFP	Pins susceptible to damage, difficult to repair bent pins	Difficult to inspect and rework, limited shelf life, costlier than QFN	Limited I/O pins, reliability issues (solder joint and warpage)	Longer die-to- die connections	Reliability issues in polymer RDL, lower I/O density than 2.5D	Costlier than 2.1D, reliability concerns
Common Application	Consumer electronics, industrial applications, legacy systems	Smartphone, tablets, automotive, telecommunic ations	Micro- controllers and micro- processors, ASICs	High performance ICs	Smartphones, IoT, wearable devices	Data centre chips, RF wireless modules, Space avionics	High performance computing segments	Data centre GPU for AI

- 1. DIP: Durable & easy to assemble, but is larger in size & accommodates a lower pin count. Isn't compatible with automated assembly. Used in legacy systems.
- 2. QFN: Compact & better thermal performance. Lower degree of testability & relative to QFN has lower pin count.
- 3. QFP: Higher density, easy to test & solder. But is mechanically susceptible to damage.
- PBGA: Even higher IO count as using entire bottom surface & better thermal performance. But difficult to inspect & more expensive.
- 5. CSP: Reduced package size, but requires more connections, peripherals & are more prone to mechanical failure.
- 20: Higher level of integration, improved efficiency & improved performance. But longer die-to-die connection.
- 7. 2.1D: Has benefits of 2D, but has RDL to improve communication speed. Stacking materials
- impacts reliability.

 8. 2.5D: Adds active interposer to connect dies. Higher IO count & lower latency. Since additional silicon is added, is more expensive & limitations on die size.

Note: Must understand the manufacturing process or use case of IC to decide on packaging.